

ABSTRACT OF THE DISCLOSURE

The invention encompasses a method of forming an insulative material along a conductive structure. A conductive structure is provided over a substrate, and an electrically insulative material is formed along at least a portion of the conductive structure. The electrically insulative material comprises at least one of $\text{Si}_x\text{O}_y\text{N}_z$ and Al_pO_q , wherein p, q, x, y and z are greater than 0 and less than 10. A dopant barrier layer is formed over the electrically insulative material. BPSG is formed over the dopant barrier layer, and the dopant barrier layer prevents dopant migration from the BPSG to the electrically insulative material. The invention also encompasses transistor structures, and methods of forming transistor structures.

OPENING STATEMENT